

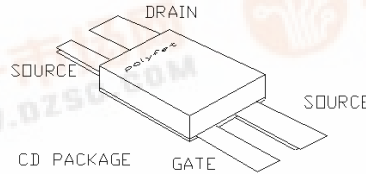


F2201S

General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features gold metal for greatly extended lifetime. Low output capacitance and high F_t enhance broadband performance



PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR

2 Watts Single Ended

Package Style CD

HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
20 Watts	12 °C/W	200 °C	-65 °C to 150 °C	0.8 A	50 V	50V	30V

RF CHARACTERISTICS (2WATTS OUTPUT)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	10			dB	$I_{dq} = 0.2 \text{ A}$, $V_{ds} = 12.5 \text{ V}$, $F = 850 \text{ MHz}$
η	Drain Efficiency		50		%	$I_{dq} = 0.2 \text{ A}$, $V_{ds} = 12.5 \text{ V}$, $F = 850 \text{ MHz}$
VSWR	Load Mismatch Toleranc			20:1	Relative	$I_{dq} = 0.2 \text{ A}$, $V_{ds} = 12.5 \text{ V}$, $F = 850 \text{ MHz}$

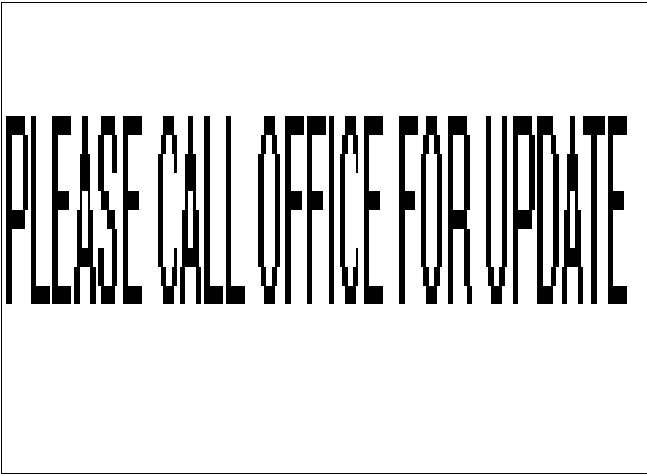
ELECTRICAL CHARACTERISTICS (EACH SIDE)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltag	40			V	$I_{ds} = 0.01 \text{ A}$, $V_{gs} = 0 \text{ V}$
I_{dss}	Zero Bias Drain Curren			0.2	mA	$V_{ds} = 12.5 \text{ V}$, $V_{gs} = 0 \text{ V}$
I_{gss}	Gate Leakage Curren			1	uA	$V_{ds} = 0 \text{ V}$, $V_{gs} = 30 \text{ V}$
Vgs	Gate Bias for Drain Curren	1		7	V	$I_{ds} = 0.02 \text{ A}$, $V_{gs} = V_{ds}$
gM	Forward Transconductanc		0.2		Mho	$V_{ds} = 10 \text{ V}$, $V_{gs} = 5 \text{ V}$
Rdson	Saturation Resistanc		2		Ohm	$V_{gs} = 20 \text{ V}$, $I_{ds} = 1.6 \text{ A}$
I_{dsat}	Saturation Curren		2.3		Amp	$V_{gs} = 20 \text{ V}$, $V_{ds} = 10 \text{ V}$
Ciss	Common Source Input Capacitanc		7.5		pF	$V_{ds} = 12.5 \text{ V}$, $V_{gs} = 0 \text{ V}$, $F = 1 \text{ MHz}$
Crss	Common Source Feedback Capacitanc		1.2		pF	$V_{ds} = 12.5 \text{ V}$, $V_{gs} = 0 \text{ V}$, $F = 1 \text{ MHz}$
Coss	Common Source Output Capacitanc		8		pF	$V_{ds} = 12.5 \text{ V}$, $V_{gs} = 0 \text{ V}$, $F = 1 \text{ MHz}$

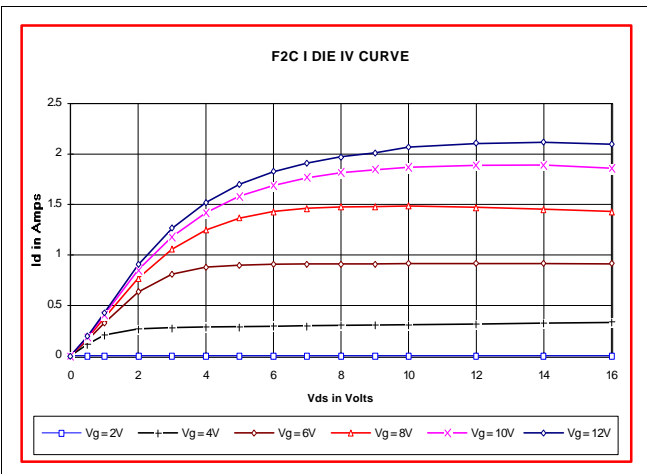


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POUT VS PIN GRAPH

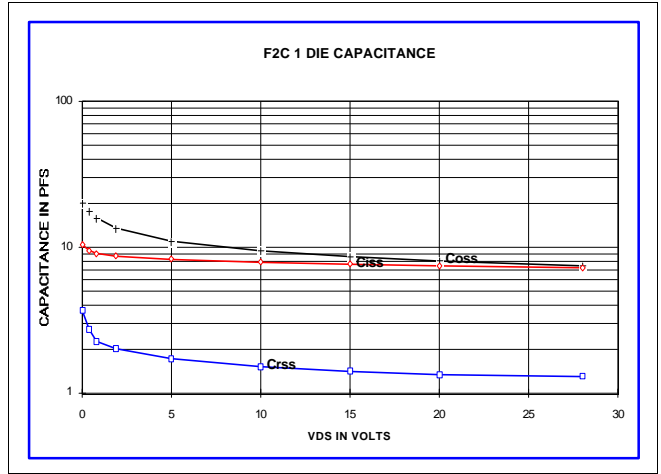


IV CURVE

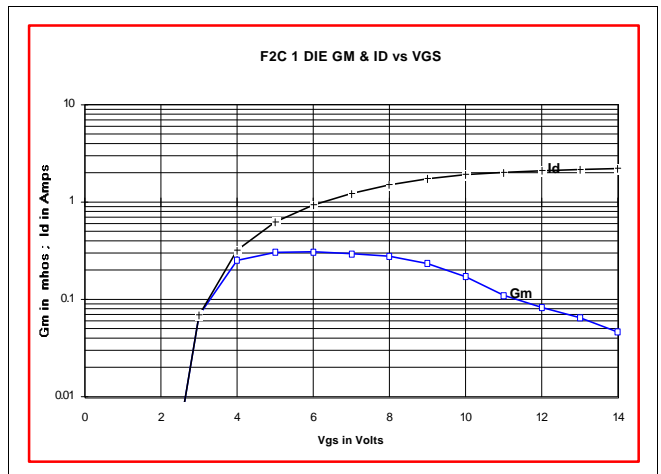


S11 AND S22 SMITH CHART

CAPACITANCE VS VOLTAGE



ID AND GM VS VGS



PACKAGE DIMENSIONS IN INCHES

